



ADVANCED ELECTRONICS LABORATORIES PROJECT

NANO-CHIP RELIABILITY GRADE HALL EFFECT SYSTEM

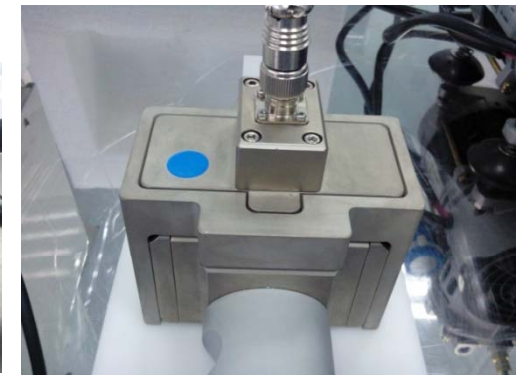
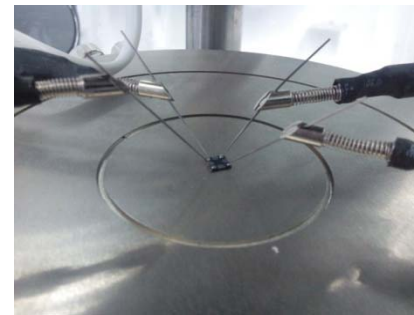
SPECIFICATIONS

| | |
|------------------------------------|--|
| Sample /Chip Size : | 10mm x 10mm ~ 15mm x 15mm |
| Operating Temperature : | Elevated, Ambient Room Temperature and 77K |
| Measurement Electronic materials : | Si,Ge,SiGe,SiC,GaAs,InGaAs,InP,GaN,ZnO, Graphene, Nano Particles etc |
| Magnetic Flux Density : | 0.68T, 1T (Variable) |
| Current Sensitivity : | 2nA |
| Input Voltage : | 1 μ V-300V |
| Carrier Density : | 10 ⁷ – 10 ²² (cm ⁻³) |



APPLICATIONS

- A measurement system using device probing
- Supports a range of DC field Hall measurements—measure mobility on wafer-scale materials and device structures as a function of temperature and field
- Vary temperatures for cryogenic and high temperature applications
- Includes intuitive software for easy system operation, data acquisition, and device and system level analysis
- Supports exporting of data for complete Hall effect multi-carrier analysis (Sheet Resistance/ Resistivity / Conductivity/ Hall Coefficient /Hall Voltage/Material/ conductivity Type/Sheet Carrier Concentration /Bulk Concentration /Mobility /Contact Check)



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